## Fu Chen

## List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/710985/publications.pdf

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		1478505	1720034
7	126	6	7
papers	citations	h-index	g-index
7	7	7	196
all docs	docs citations	times ranked	citing authors

#	Article	IF	CITATIONS
1	Gate leakage mechanisms in normally off p-GaN/AlGaN/GaN high electron mobility transistors. Applied Physics Letters, 2018, 113, .	3.3	65
2	Studies on Fabrication and Reliability of GaN High-Resistivity-Cap-Layer HEMT. IEEE Transactions on Electron Devices, 2018, 65, 1314-1320.	3.0	23
3	Improvement of Breakdown Voltage and ON-Resistance in Normally-OFF AlGaN/GaN HEMTs Using Etching-Free p-GaN Stripe Array Gate. IEEE Transactions on Electron Devices, 2021, 68, 5041-5047.	3.0	13
4	High-resistivity unintentionally carbon-doped GaN layers with nitrogen as nucleation layer carrier gas grown by metal-organic chemical vapor deposition. AIP Advances, 2017, 7, 125018.	1.3	9
5	Influence factors and temperature reliability of ohmic contact on AlGaN/GaN HEMTs. AIP Advances, 2018, 8, .	1.3	8
6	Enhancement-mode n-GaN gate p-channel heterostructure field effect transistors based on GaN/AlGaN 2D hole gas. Applied Physics Letters, 2019, 115, .	3.3	6
7	Study on shallow donor-type impurities of GaN epilayer regrown by epitaxial lateral overgrowth technique. Applied Physics Letters, $2021,118,.$	3.3	2